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P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
-60	0.024 at V _{GS} = - 10 V	- 40		
-00	0.029 at V _{GS} = - 4.5 V	- 30		

FEATURES

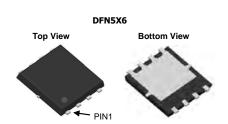
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

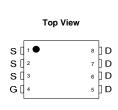
APPLICATIONS

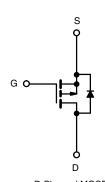
- Notebook
 - Load Switch



RoHS







P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	Limit	UNIT	
Drain-Source Voltage		V_{DS}	- 60	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I_	- 40		
	T _A = 70 °C	l _D	- 36		
Pulsed Drain Current		I _{DM}	- 160	Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 40		
Avalanche Current	L = 0.1 mH	I _{AS}	- 37		
Single Pulse Avalanche Energy	L = 0.111111	E _{AS}	135	mJ	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	37	W	
	T _A = 70 °C	ГD	23.7		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	
Soldering Recommendations (Peak Temperature) b, c			260		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	20	45		
	Steady State		40	60	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.3	1.8		

Notes

- a. Surface mounted on 1" x 1" FR4 board.
- b. TheDFN5x6isa leadlesspackage. The endof thelead terminalisexposedcopper (not plated) as a result of thesingulation process in manufacturing. A solderfillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequatebottom side solder interconnection.
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

Rev. 1.0



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1	-	- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zana Oata Vallana Busin Ourmant		V _{DS} = - 48 V, V _{GS} = 0 V	V _{DS} = - 48 V, V _{GS} = 0 V		- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 48 V, V _{GS} = 0 V, T _J = 70 °C	-	-	- 10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 40	-	-	Α	
5 . 6 . 6	_	V _{GS} = - 10 V, I _D = - 15 A	-	0.024	0.030		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 10 A	-	0.029	0.040	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 15 A	-	28	-	S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1 A, V _{GS} = 0 V	-	- 0.7	- 1.0	V	
Dynamic ^b							
Input Capacitance	C _{iss}		-	1610	-		
Output Capacitance	C _{oss}	V _{DS} = - 30 V, V _{GS} = 0 V, f = 1 MHz		202	-	pF	
Reverse Transfer Capacitance	C _{rss}		-	19	-	†	
Total Gate Charge	Qg		-	56	-		
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -15 \text{ A}$	-	13	-	nC	
Gate-Drain Charge	Q_{gd}		1	12	-		
Gate Resistance	R_g		1	2.5	-	Ω	
Turn-On Delay Time	t _{d(on)}		-	20	-		
Rise Time	t _r	V_{DD} = - 30 V, R_L = 30 Ω	-	29	-		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 15 A, V_{GEN} = - 10 V, R_g = 6 Ω	-	65	-	ns	
Fall Time	t _f		-	23	-		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 15 A, dI/dt = 100 A/μs	-	25	-	ns	
Source-Drain Reverse Recovery Charge	Q_{rr}	I _F = - 15 A, dI/dt = 100 A/μs	-	148	-	nC	

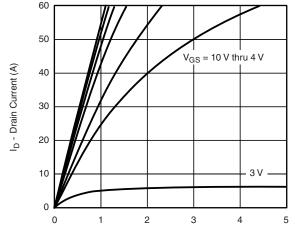
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

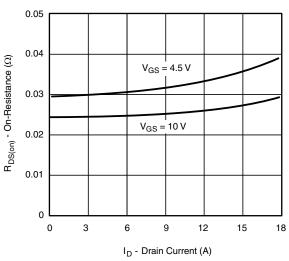


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

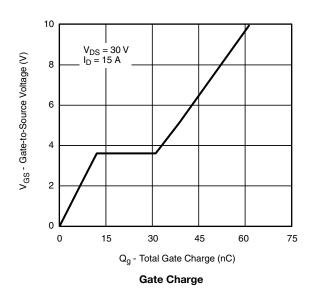


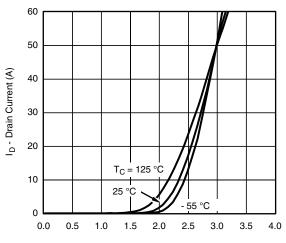
V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics



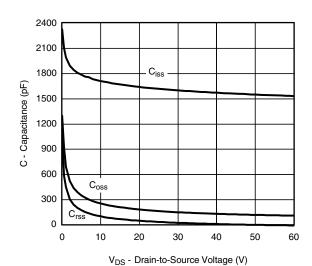
On-Resistance vs. Drain Current



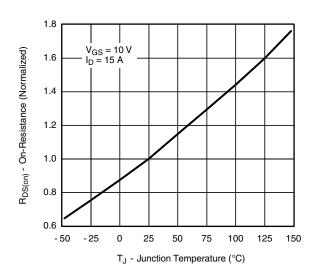


V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



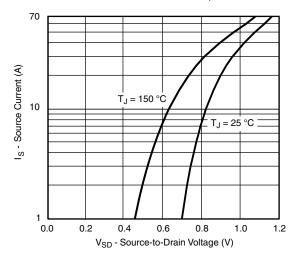
Capacitance



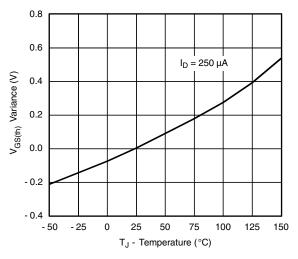
On-Resistance vs. Junction Temperature



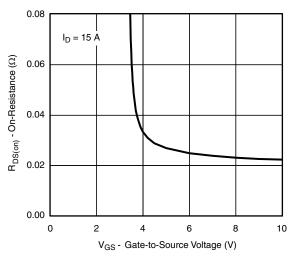
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



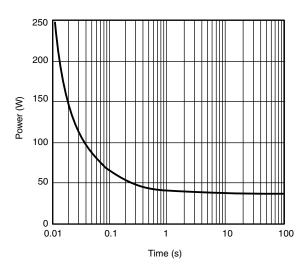
Source-Drain Diode Forward Voltage



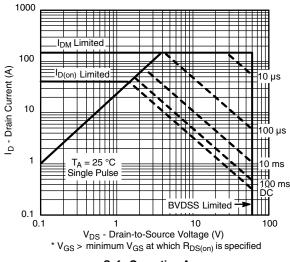
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

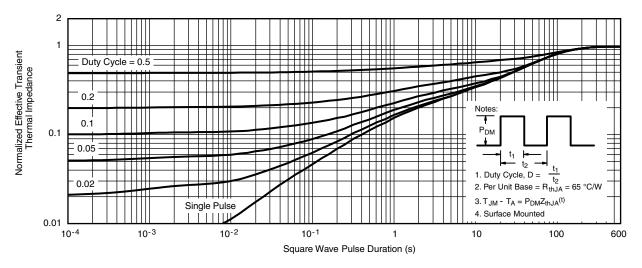


Single Pulse Power, Junction-to-Ambient

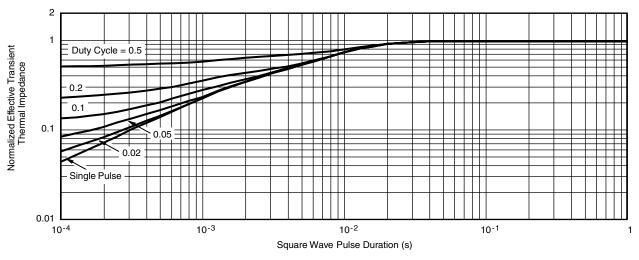




TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



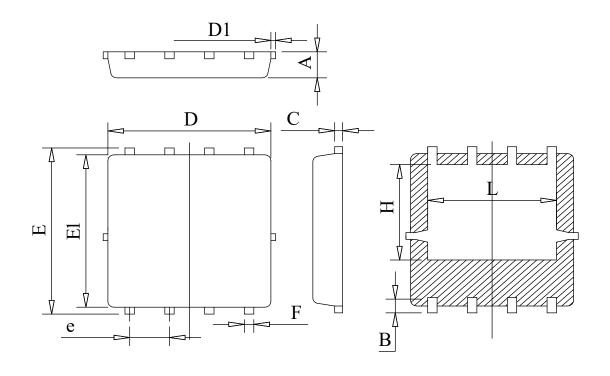
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25





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